



**RF-3475-76**

**M. Sc. - I Examination**

**April / May - 2010**

**Electronics : Paper - III**

*(Communication Electronics - I and Solid State Devices)*

Time : Hours]

[Total Marks : 52

**RF-3475**

**Instructions :**

(1)

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| नीचे दर्शाविए निशानीवाणी विगतो उत्तरवही पर अवश्य लपवी.<br>Fillup strictly the details of signs on your answer book.                            | Seat No. :                                       |
| Name of the Examination :  | <input type="text"/>                             |
| <input type="text" value="M. Sc. - 1"/>  | <input type="text"/>                             |
| Name of the Subject :  | <input type="text"/>                             |
| <input type="text" value="Electronics - 3"/>   | <input type="text"/>                             |
| Subject Code No. : <input type="text" value="3"/> <input type="text" value="4"/> <input type="text" value="7"/> <input type="text" value="5"/> | <input type="text" value="Student's Signature"/> |
| Section No. (1, 2,.....) : <input type="text" value="1"/>  |  |

- (2) Answers to the two sections must be written in separate answer books.
- (3) Figures to right hand side of each question indicate full marks.
- (4) Assume the data if necessary.

- 1 (a) Discuss the different forms of pulse modulation. 2
- (b) Give the comparison of various amplitude modulation systems. 3
- (c) The signal  $v(t) = \cos 5\pi t + 0.5 \cos 10\pi t$  is instantaneously sampled. The interval between samples is  $T_S$ . 3
- (i) Find the minimum allowable value for  $T_S$

(ii) If the sampling signal is  $S(t) = 5 \sum_{k=-\infty}^{\infty} \delta(t - 0.1k)$

the sampled signal  $v_s(t) = v(t)s(t)$  consists of a train of impulses each with a different strength

$$v_s(t) = \sum_{k=-\infty}^{\infty} I_k \delta(t - 0.1k), \text{ Find } I_0, I_1 \text{ and } I_2.$$

- 2 (a) Explain the importance of second order phase locked loop. Explain the operation of it. 5
- (b) The waveform  $v(t) = (1 + \mu \cos w_m t)$ , with  $(\mu \leq 1)$  is applied to the diode demodulator. Show that, if the demodulator output is to follow the envelope of  $v(t)$ , it is required that at any time to 4

$$\frac{1}{RC} \geq w_m \left( \frac{\mu \sin w_m t_o}{1 + \mu \cos w_m t_o} \right)$$

OR

- 2 (a) With necessary block diagram, explain the working of a delta modulator system. What is the drawback of this system. 5
- (b) For a signal  $v(t) = A_1 \cos(w_1 t + \theta_1) + A_2 \cos(w_2 + \theta_2)$ . Find the autocorrelation function  $R(y)$  and the power of a signal  $v(t)$ . 4

- 3 (a) Discuss the importance of sampling in communication system. State and prove sampling theorem. 5
- (b) The first stage of a two stage amplifier has voltage gain of 12, input resistance of 500  $\Omega$ , equivalent noise resistance of 1200  $\Omega$  and output resistor of 20 k $\Omega$ . The second stage has voltage gain of 16, input resistance of 10 k $\Omega$ , equivalent noise resistance of 12 k $\Omega$  and output resistor of 600 k $\Omega$ . Calculate the equivalent input noise resistance for this two stage amplifier. Also compute the total voltage at the input of the first stage given that the bandwidth of amplifier is 10 KH<sub>2</sub> and T = 27°C. 4

OR

- 3 (a) (i) Explain the concept of random process. 4  
(ii) Define the cumulative distribution function and show that it is a non decreasing function. 1
- (b) Derive the radar range equation. Discuss the factors influencing the maximum radar range. 4



- 6 (a) Draw the energy band diagram of p-n junction diode showing the intrinsic Fermi level, quasi Fermi level and carrier distributions under the forward and reverse biased conditions and comment on it. 5
- (b) Using basic device model, draw the energy band diagrams of two isolated semiconductors (forming heterojunctions) in which the space charge neutrality is assumed to exist in each region and explain it. 4
- OR
- 6 (a) Using necessary I-V characteristics, explain three different regions of transistor switching. 5
- (b) Using thermionic emission theory, derive the equation of the carrier density flowing the metal-semiconductor junction diode. 4

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